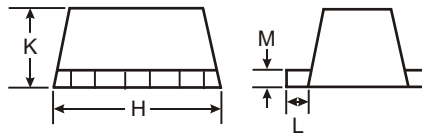
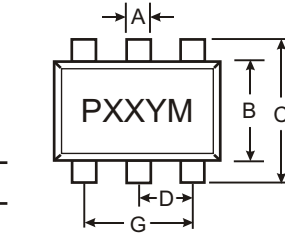


Features

- Epitaxial Planar Die Construction
- Complementary NPN Types Available (DDC)
- Built-In Biasing Resistors
- Lead-Free Device

Mechanical Data

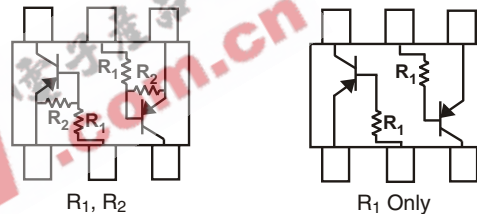
- Case: SOT-563, Molded Plastic
- Case material - UL Flammability Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Finish - Matte Tin Solderable per MIL-STD-202, Method 208 (Note 2)
- Terminal Connections: See Diagram
- Weight: 0.005 grams (approx.)



SEE NOTE 1

SOT-563			
Dim	Min	Max	Typ
A	0.15	0.30	0.25
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	0.50		
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.56	0.60	0.60
L	0.15	0.25	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

P/N	R1	R2	MARKING
DDA124EH	22K Ω	22K Ω	P17
DDA144EH	47K Ω	47K Ω	P20
DDA143EH	4.7K Ω	4.7K Ω	P08
DDA114YH	10K Ω	47K Ω	P14
DDA123JH	2.2K Ω	47K Ω	P06
DDA114EH	10K Ω	10K Ω	P13
DDA143TH	4.7K Ω	-	P07
DDA114TH	10K Ω	-	P12



SCHEMATIC DIAGRAM, TOP VIEW

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	V _{CC}	50	V
Input Voltage	V _{IN}	+10 to -40 +10 to -40 +10 to -30 +6 to -40 +5 to -12 +10 to -40 +5 V _{max} +5 V _{max}	V
Output Current	I _O	-30 -30 -100 -70 -100 -50 -100 -100	mA
Output Current	I _C (Max)	-100	mA
Power Dissipation	P _d	150	mW
Thermal Resistance, Junction to Ambient Air (Note 3)	R _{θJA}	833	°C/W
Operating and Storage and Temperature Range	T _j , T _{STG}	-55 to +150	°C

- Note:
1. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).
 2. If lead-bearing terminal plating is required, please contact your Diodes Inc. sales representative for availability and minimum order details.
 3. Mounted on FR4 Board with recommended pad layout at <http://www.diodes.com/datasheets/ap02001.pdf>.

Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic (DDA143TH & DDA114TH only)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-50	—	—	V	I _C = -50μA
Collector-Emitter Breakdown Voltage	BV _{CEO}	-50	—	—	V	I _C = -1mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	—	—	V	I _E = -50μA
Collector Cutoff Current	I _{CBO}	—	—	-0.5	μA	V _{CB} = -50V
Emitter Cutoff Current	I _{EBO}	—	—	-0.5	μA	V _{EB} = -4V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	—	-0.3	V	I _C /I _B = -2.5mA / -0.25mA I _C /I _B = -1mA / -0.1mA DDA143TH DDA114TH
DC Current Transfer Ratio	h _{FE}	100	250	600	—	I _C = -1mA, V _{CE} = -5V
Gain-Bandwidth Product*	f _T	—	250	—	MHz	V _{CE} = -10V, I _E = 5mA, f = 100MHz

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
Input Voltage	V _{I(off)}	DDA124EH	-0.5	-1.1	—	V	V _{CC} = -5V, I _O = -100μA
		DDA144EH	-0.5	-1.1			
Input Voltage	V _{I(on)}	DDA143EH	-0.5	-1.1	—	V	V _O = -0.3V, I _O = -5mA
		DDA114YH	-0.3	—			
Input Voltage	V _{I(on)}	DDA123JH	-0.5	—	—	V	V _O = -0.3V, I _O = -2mA
		DDA114EH	-0.5	-1.1			
Output Voltage	V _{O(on)}	DDA124EH	—	-1.9	-3.0	V	V _O = -0.3V, I _O = -20mA
		DDA144EH	—	-1.9			
Output Voltage	V _{O(on)}	DDA143EH	—	-1.9	-3.0	V	V _O = -0.3V, I _O = -1mA
		DDA114YH	—	—			
Output Voltage	V _{O(on)}	DDA123JH	—	-1.1	-3.0	V	V _O = -0.3V, I _O = -5mA
		DDA114EH	—	-1.9			
Output Voltage	V _{O(on)}	DDA124EH	—	-0.1	-0.3	V	V _O = -0.3V, I _O = -10mA
		DDA144EH	—	—			
Output Voltage	V _{O(on)}	DDA143EH	—	—	-0.3	V	I _O /I _I = -10mA / -0.5mA
		DDA114YH	—	—			
Output Voltage	V _{O(on)}	DDA123JH	—	—	-0.3	V	I _O /I _I = -10mA / -0.5mA
		DDA114EH	—	—			
Input Current	I _I	DDA124EH	—	—	-0.36	mA	V _I = -5V
		DDA144EH	—	—			
Input Current	I _I	DDA143EH	—	—	-0.18	mA	V _I = -5V
		DDA114YH	—	—			
Input Current	I _I	DDA123JH	—	—	-1.8	mA	V _I = -5V
		DDA114EH	—	—			
Input Current	I _I	DDA123JH	—	—	-0.88	mA	V _I = -5V
		DDA114EH	—	—			
Output Current	I _{O(off)}	DDA124EH	—	—	-0.5	μA	V _{CC} = -50V, V _I = -0V
		DDA144EH	—	—			
Output Current	I _{O(off)}	DDA143EH	—	—	-0.5	μA	V _{CC} = -50V, V _I = -0V
		DDA114YH	—	—			
Output Current	I _{O(off)}	DDA123JH	—	—	-0.5	μA	V _{CC} = -50V, V _I = -0V
		DDA114EH	—	—			
DC Current Gain	G _I	DDA124EH	56	—	—	—	V _O = -5V, I _O = -5mA
		DDA144EH	68	—			
DC Current Gain	G _I	DDA143EH	20	—	—	—	V _O = -5V, I _O = -5mA
		DDA114YH	68	—			
DC Current Gain	G _I	DDA123JH	80	—	—	—	V _O = -5V, I _O = -10mA
		DDA114EH	30	—			
DC Current Gain	G _I	DDA123JH	80	—	—	—	V _O = -5V, I _O = -10mA
		DDA114EH	30	—			
Gain-Bandwidth Product*	f _T	—	250	—	MHz	V _{CE} = -10V, I _E = -5mA, f = 100MHz	

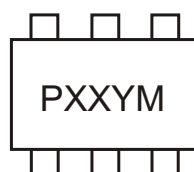
* Transistor - For Reference Only

Ordering Information (Note 4)

Device	Packaging	Shipping
DDA124EH-7	SOT-563	3000/Tape & Reel
DDA144EH-7	SOT-563	3000/Tape & Reel
DDA143EH-7	SOT-563	3000/Tape & Reel
DDA114YH-7	SOT-563	3000/Tape & Reel
DDA123JH-7	SOT-563	3000/Tape & Reel
DDA114EH-7	SOT-563	3000/Tape & Reel
DDA143TH-7	SOT-563	3000/Tape & Reel
DDA114TH-7	SOT-563	3000/Tape & Reel

Notes: 4. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



PXX = Product Type Marking Code (See Page 1)

YM = Date Code Marking

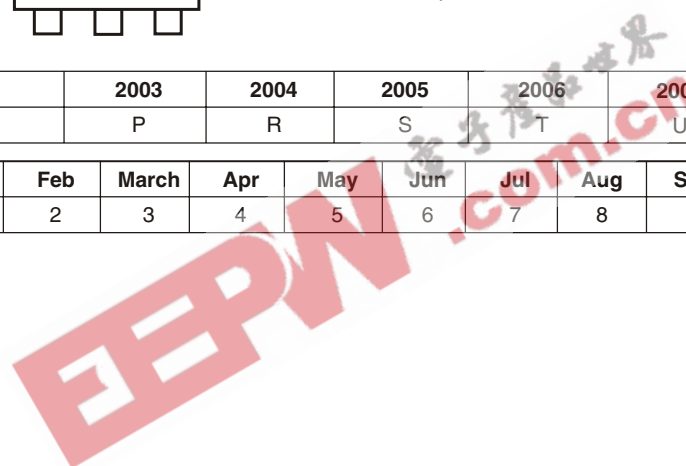
Y = Year ex: P = 2003

M = Month ex: 9 = September

Date Code Key

Year	2003	2004	2005	2006	2007	2008	2009
Code	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D



TYPICAL CURVES - DDA143EH

NEW PRODUCT

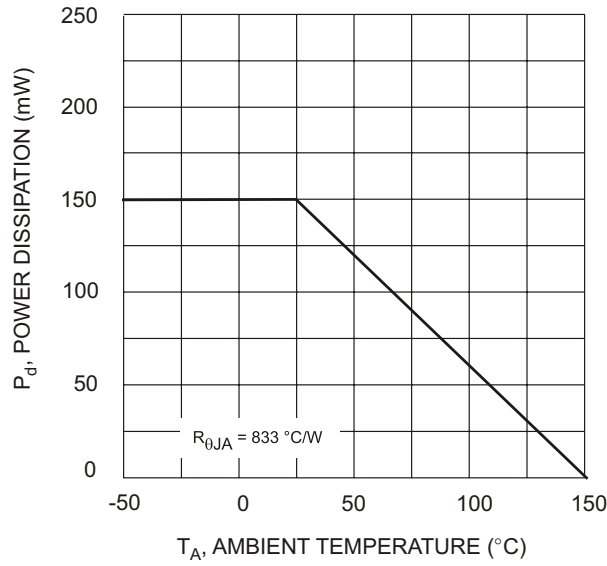


Fig. 1 Derating Curve

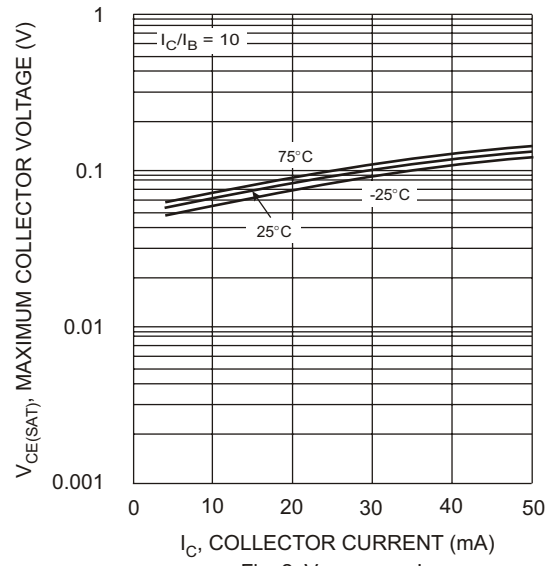


Fig. 2 $V_{CE(SAT)}$ vs. I_C

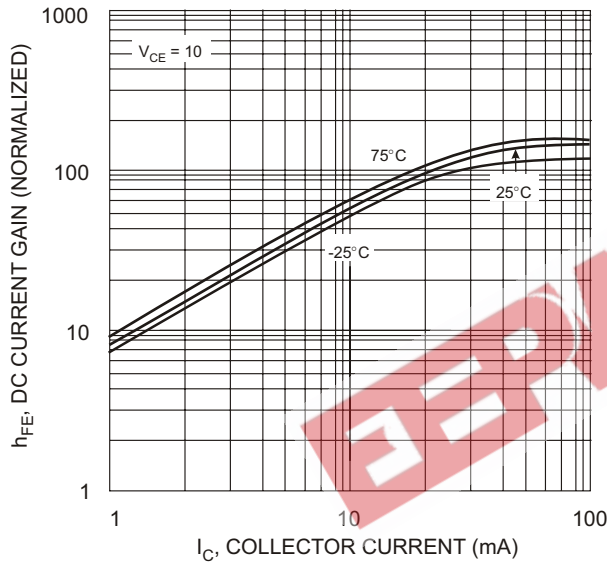


Fig. 3 DC Current Gain

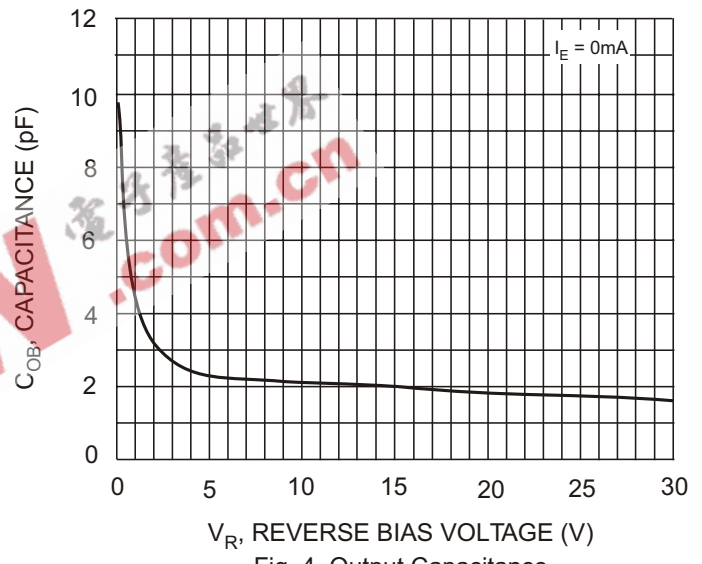


Fig. 4 Output Capacitance

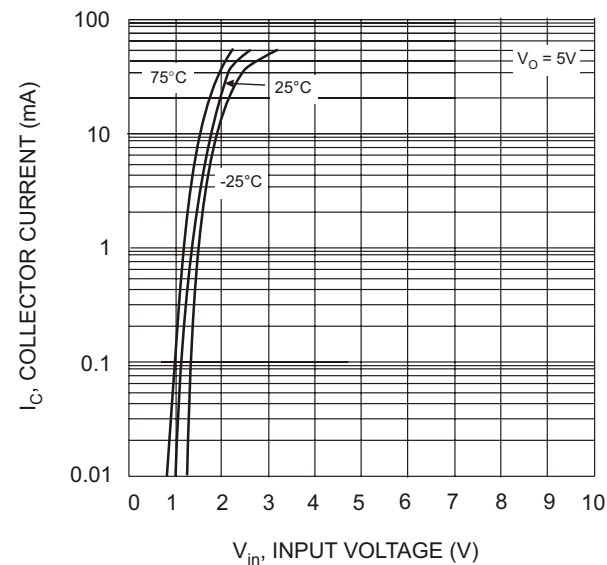


Fig. 5 Collector Current Vs. Input Voltage

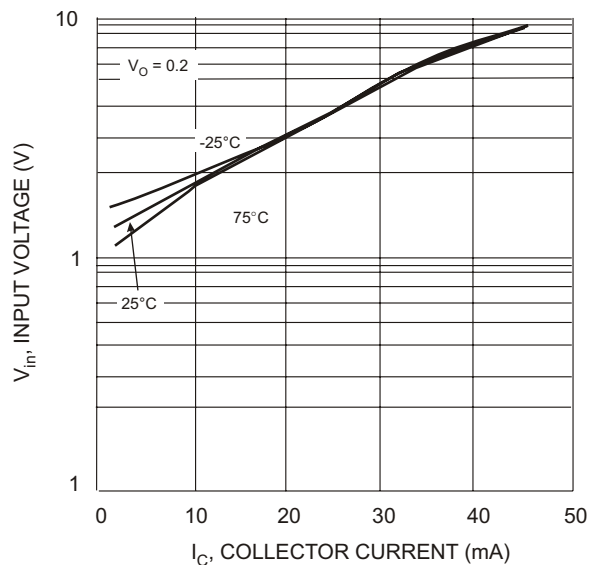


Fig. 6 Input Voltage vs. Collector Current